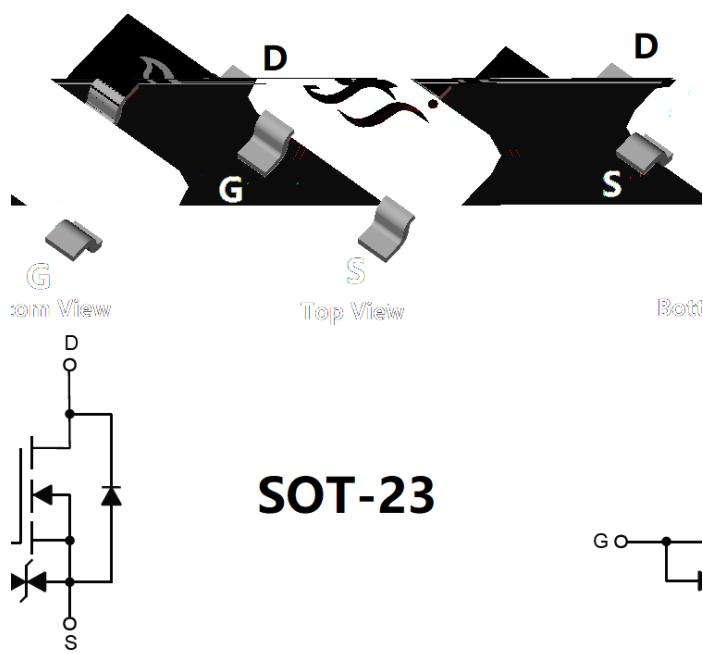




2N7002KC

N-Channel Enhancement Mode Field Effect Transistor



Product Summary

V_{DS}	60V
I_D	300mA
$R_{DS(ON)}$ (at $V_{GS}=10V$)	2.5ohm
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	3.0ohm
Gate-Source ESD Rating Up to 2KV (HBM)	

General Description

Trench Power MV MOSFET technology
 Voltage controlled small signal switch
 Low input Capacitance
 Fast Switching Speed
 Low Input / Output Leakage
 Moisture Sensitivity Level 1
 Epoxy Meets UL 94 V-0 Flammability Rating
 Halogen Free

Applications

Battery operated systems
 Solid-state relays
 Direct logic-level interface TTL/CMOS

Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V_{DS}	60	V
Gate-source Voltage		V_{GS}	20	V
Drain Current	$T_A=25^\circ C$ @ Steady State	I_D	300	mA
	$T_A=70^\circ C$ @ Steady State		240	
Pulsed Drain Current ^A		I_{DM}	1.5	A
Total Power Dissipation @ $T_A=25^\circ C$		P_D	300	mW
Thermal Resistance Junction-to-Ambient @ Steady State ^B		R_{JA}	416	/ W
Junction and Storage Temperature Range		T_J, T_{STG}	-55 +150	

Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
2N7002KC	F2	72KC.	3000	30000	120000	reel



2N7002KC

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}} = 0\text{V}, I_{\text{D}} = 250\text{mA}$	60			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}} = 60\text{V}, V_{\text{GS}} = 0\text{V}$			1	
Gate-Body Leakage Current	I_{GSS}	$V_{\text{GS}} = 20\text{V}, V_{\text{DS}} = 0\text{V}$			10	
Gate Threshold Voltage	$V_{\text{GS(th)}}$	$V_{\text{DS}} = V_{\text{GS}}, I_{\text{D}} = 250\text{mA}$	1	1.5	2.5	V
Static Drain-Source On-Resistance	$R_{\text{DS(ON)}}$	$V_{\text{GS}} = 10\text{V}, I_{\text{D}} = 300\text{mA}$		1.9	2.5	
		$V_{\text{GS}} = 4.5\text{V}, I_{\text{D}} = 200\text{mA}$		2.0	3.0	
Diode Forward Voltage	V_{SD}	$I_{\text{S}} = 300\text{mA}, V_{\text{GS}} = 0\text{V}$			1.2	V
Maximum Body-Diode Continuous Current	I_{S}				300	mA
Forward Transconductance	g_{FS}	$V_{\text{DS}} = 5\text{V}, I_{\text{D}} = 0.3\text{A}$		0.13		S
Dynamic Parameters						
Input Capacitance	C_{iss}	$V_{\text{DS}} = 30\text{V}, V_{\text{GS}} = 0\text{V}, f = 1\text{MHz}$		21		pF
Output Capacitance	C_{oss}			9		
Reverse Transfer Capacitance	C_{rss}			4		
Switching Parameters						
Total Gate Charge	Q_{g}	$V_{\text{GS}} = 10\text{V}, V_{\text{DS}} = 30\text{V}, I_{\text{D}} = 0.3\text{A}$		1.22	2.4	nC
Gate-Source Charge	Q_{gs}			0.5		
Gate-Drain Charge	Q_{gd}			0.18		
Reverse Recovery Charge	Q_{rr}	$V_{\text{GS}} = 0\text{V}, I_{\text{S}} = 300\text{mA}, V_{\text{R}} = 25\text{V}, \frac{dI}{dt} = 100\text{A}/\text{s}$		3.6		ns
Reverse Recovery Time	t_{rr}			16		
Turn-on Delay Time	$t_{\text{D(on)}}$			7		
Turn-on Rise Time	t_{r}	$V_{\text{GS}} = 10\text{V}, V_{\text{DD}} = 50\text{V}, I_{\text{D}} = 200\text{mA}, R_{\text{GEN}} = 50\Omega$		19		ns
Turn-off Delay Time	$t_{\text{D(off)}}$			20		
Turn-off fall Time	t_{f}			84		

A. Pulse Test: Pulse Width 300us, Duty cycle 2%.

B. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch.



2N7002KC

Typical Performance Characteristics

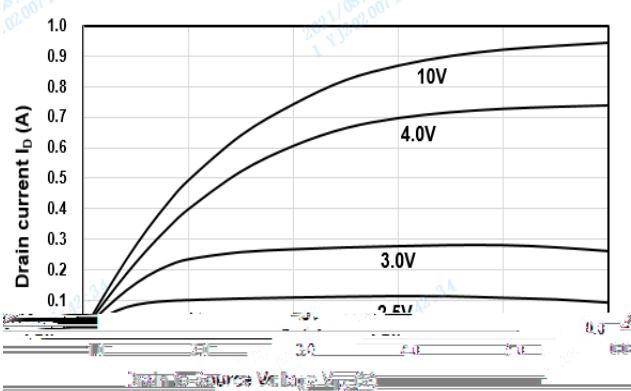


Figure1. Output Characteristics

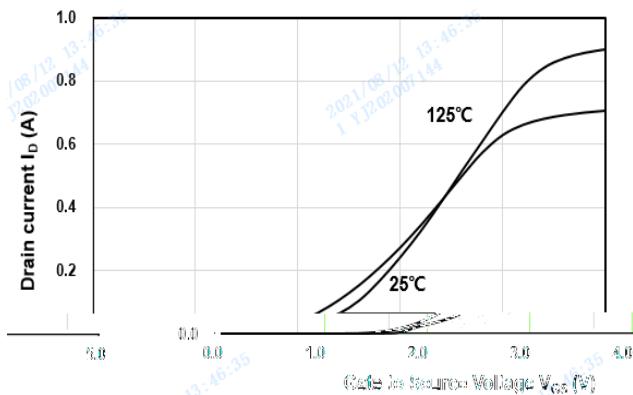


Figure2. Transfer Characteristics

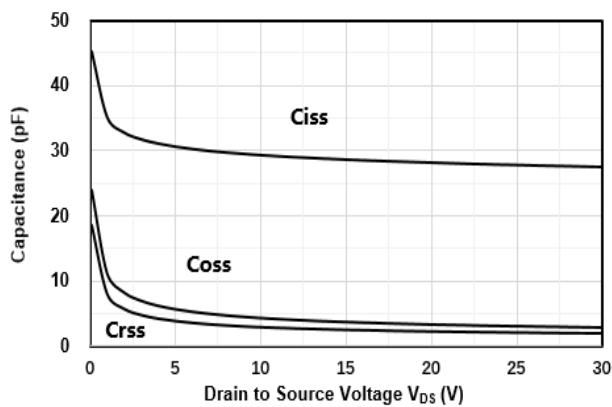


Figure3. Capacitance Characteristics

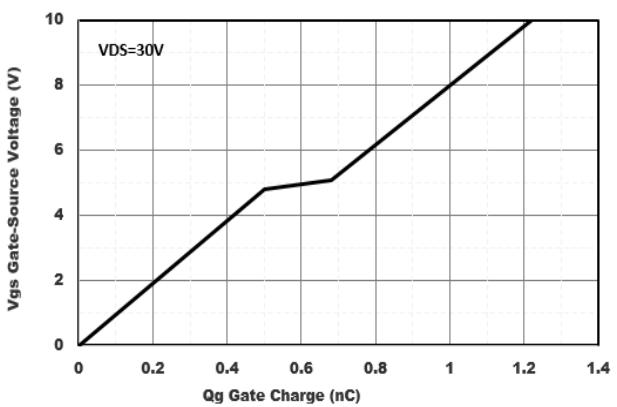


Figure4. Gate Charge

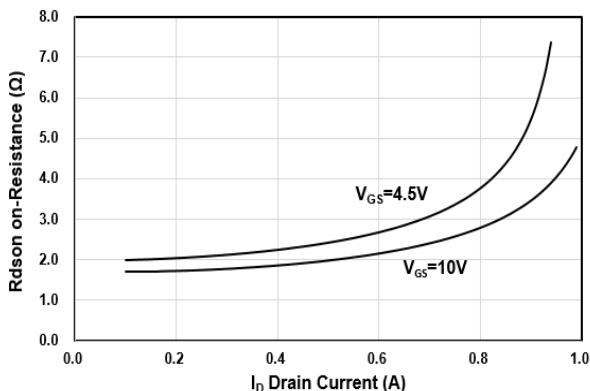


Figure5. Drain-Source on Resistance

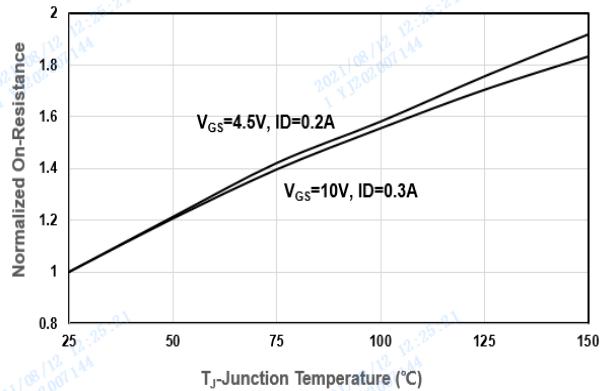


Figure6. Drain-Source on Resistance



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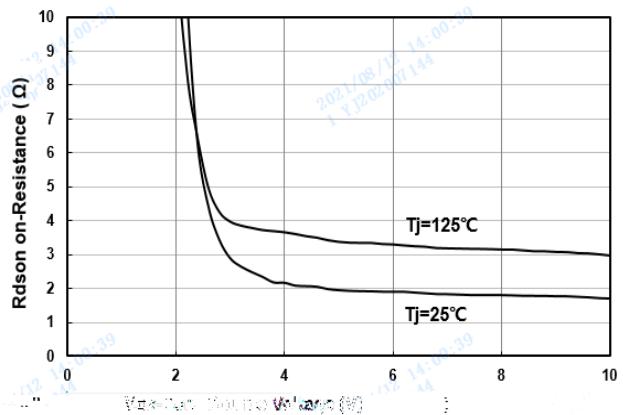


Figure7. On-Resistance vs V_{GS}

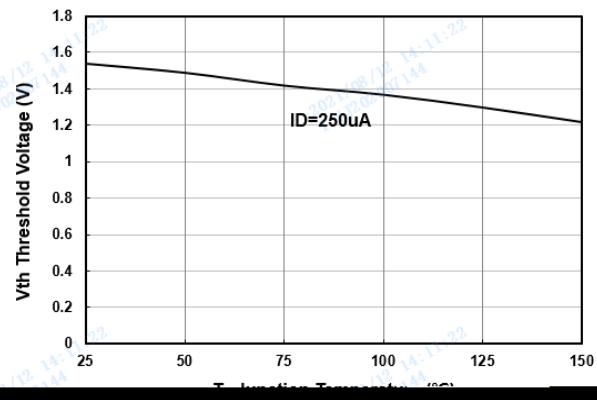


Figure8. Threshold Voltage vs Temperature

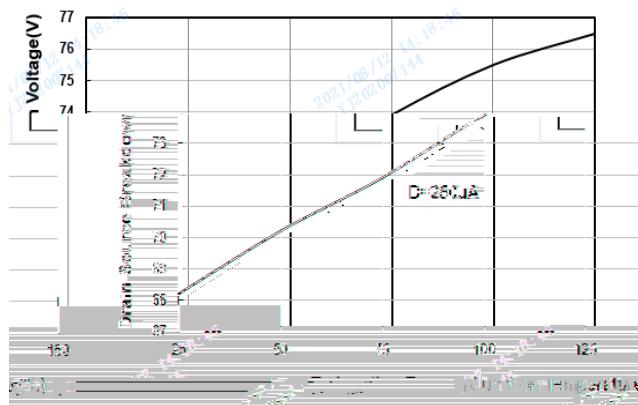


Figure9. Breakdown Voltage vs Temperature

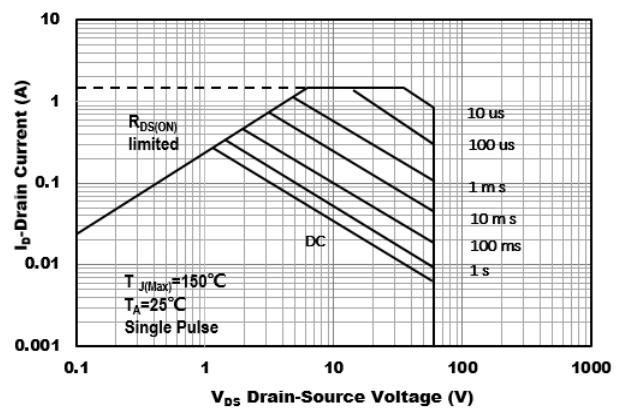


Figure10. Safe Operation Area

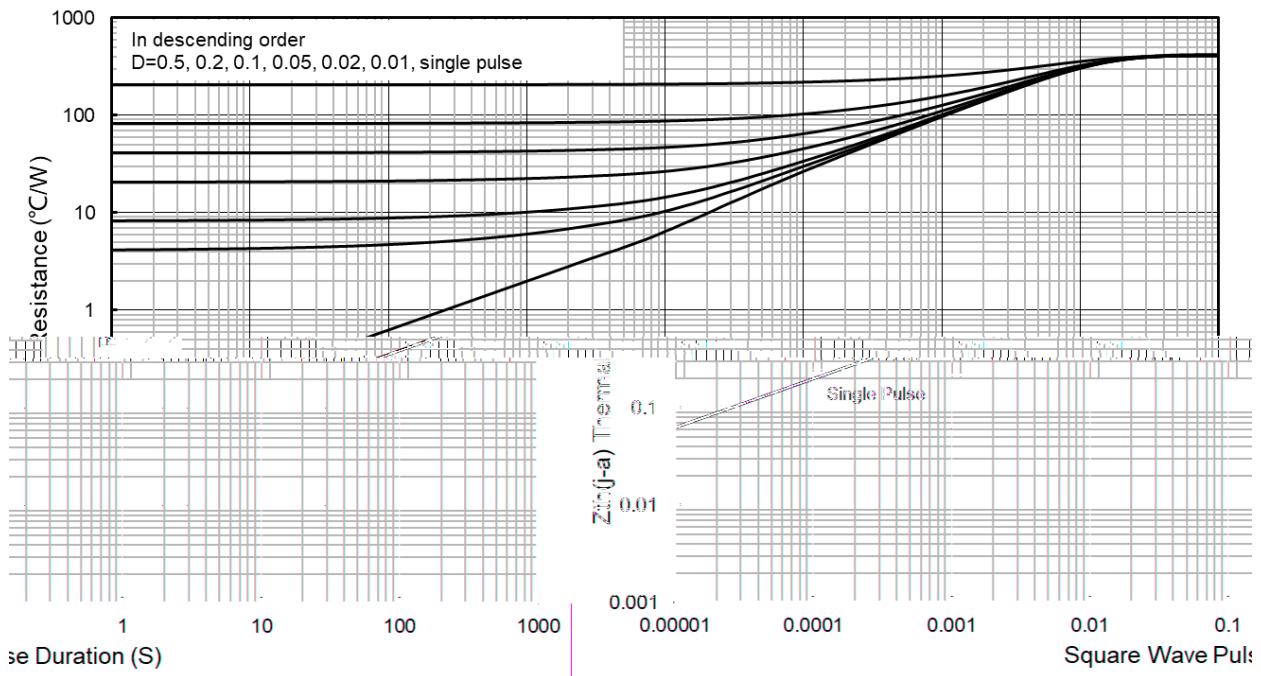
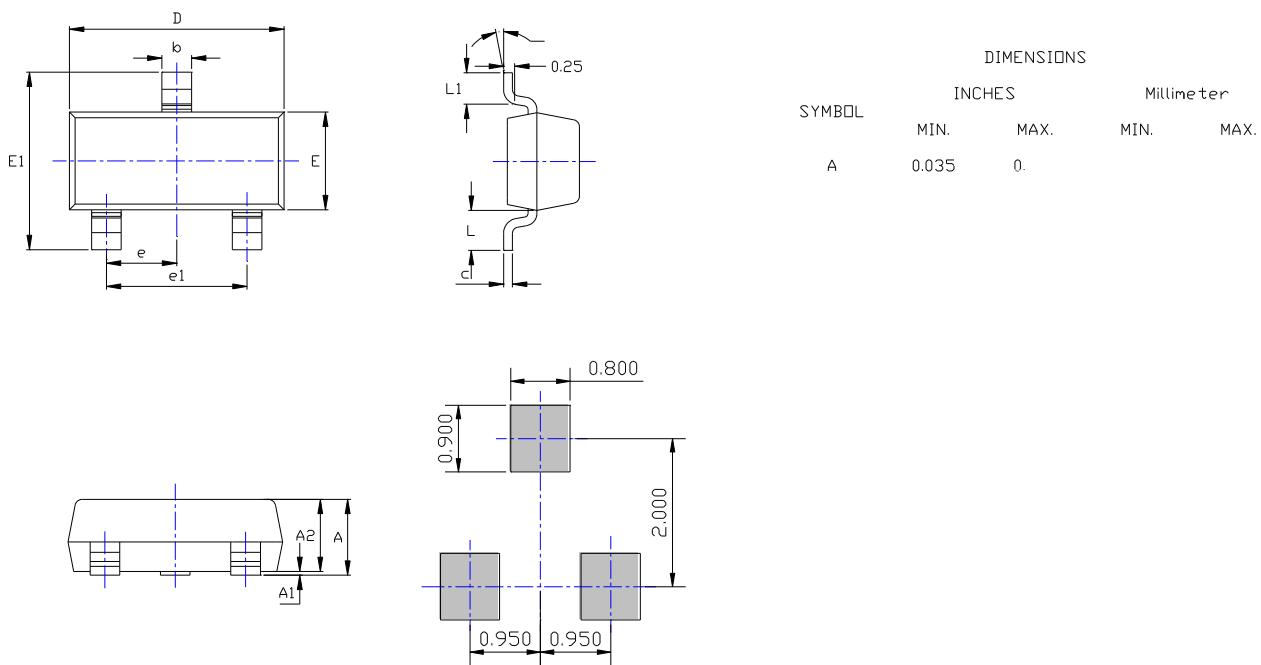


Figure11. Maximum Transient Thermal Impedance



SOT-23 Package information



p 1#®1 ®



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